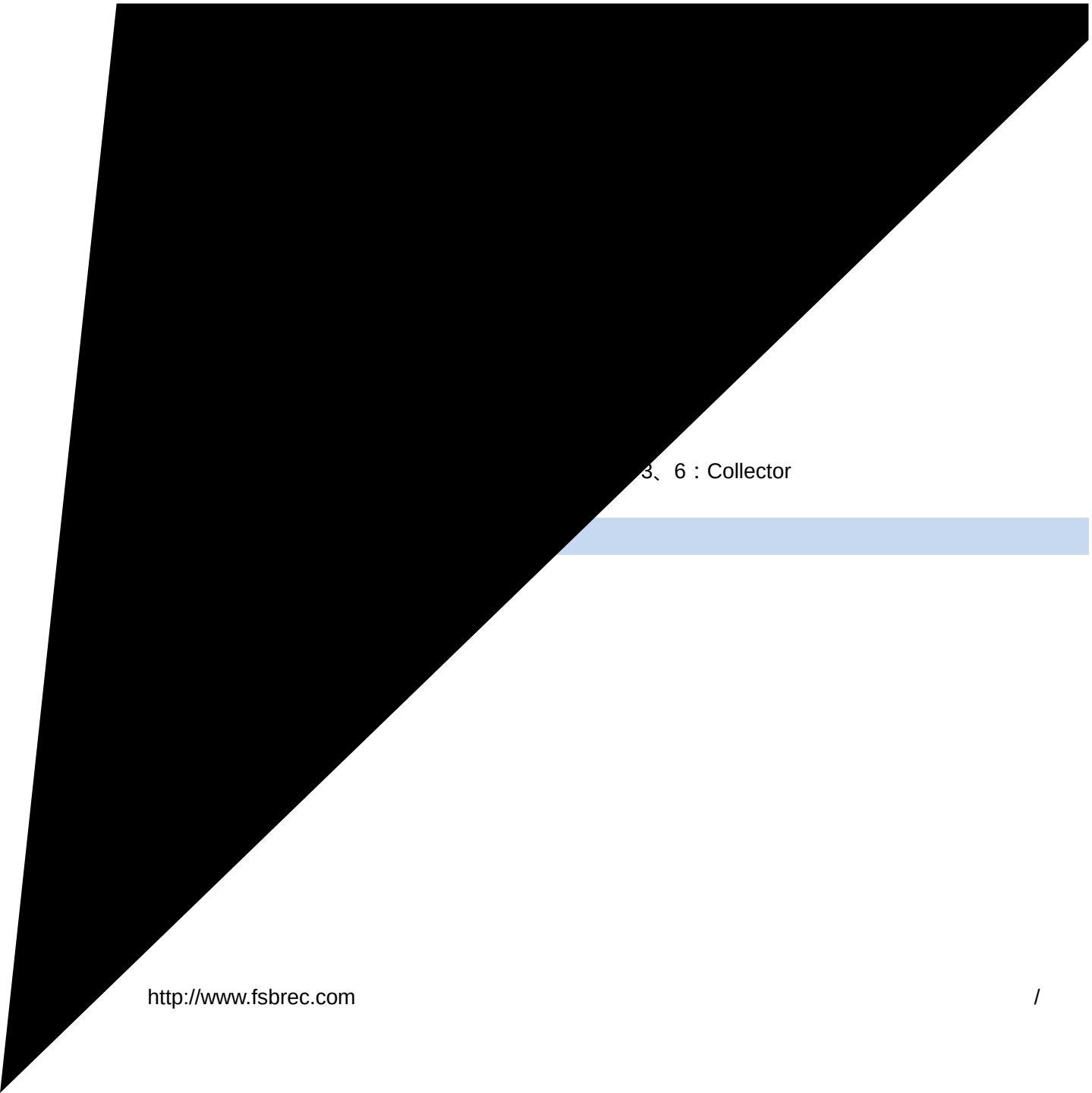
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SOT-363 塑封封装双 NPN 半导体三极管。
Double silicon NPN transistor in a SOT-363 Plastic Package.

低电压，低电流。无卤产品。
Low current, Low voltage。HF Product.

用于普通放大及开关。
General purpose amplifier and switching.



3、6：Collector

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	40	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	200	mA
Collector Power Dissipation	P_C	200	mW
	*P_C	350	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range c	T_{stg}	-55 150	℃

*When mounted on a 7×5×0.6mm ceramic board

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=10μA I_E=0	60			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA I_B=0	40			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=10μA I_C=0	6.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=30V I_E=0			0.05	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=3.0V I_C=0			0.05	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=1.0V I_C=10mA	100		300	
	$h_{FE(2)}$	V_{CE}=1.0V I_C=100mA	30			
	$h_{FE(3)}$	V_{CE}=1.0V I_C=50mA	60			
	$h_{FE(4)}$	V_{CE}=1.0V I_C=1.0mA	70			
	$h_{FE(5)}$	V_{CE}=1.0V I_C=0.1mA	40			
Collector-Emitter Saturation Voltage	$V_{CE(sat)(1)}$	I_C=10mA I_B=1.0mA			0.2	V
	$V_{CE(sat)(2)}$	I_C=50mA I_B=5.0mA			0.3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)(1)}$	I_C=10mA cS I_B=1.0mA	0.65		0.85	V

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Note:

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Product Type Code

Lot No. Code, code change with Lot No.

Re

e for IR Reflow Soldering(Pb-Free)

			Note:
1		60 90sec;	1.Preheating:150~180℃, Time:60~90sec.
2		5±0.5sec;	2.Peak Temp.:245±5℃, Duration:5±0.5sec.
3		10℃/sec.	3. Cooling Speed: 2~10℃/sec.

260	10±1 sec.	Temp.:260±5℃	Time:10±1 sec

EEL

Package Type 封装形式	Units 包装数量			
J				